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DG441B, DG442B

Vishay Siliconix

Improved Quad SPST CMOS Analog Switches

DESCRIPTION

The DG441B, DG442B are monolithic quad analog switches designed to provide high speed, low error switching of analog and audio signals. The DG441B, DG442B are upgrades to the original DG441, DG442.

Combining low on-resistance ($45\ \Omega$, typ.) with high speed (t_{ON} 120 ns, typ.), the DG441B, DG442B are ideally suited for Data Acquisition, Communication Systems, Automatic Test Equipment, or Medical Instrumentation. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

The DG441B, DG442B are built using Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

When on, each switch conducts equally well in both directions and blocks input voltages to the supply levels when off.

FEATURES

- Low On-Resistance: $45\ \Omega$
- Low Power Consumption: 1 mW
- Fast Switching Action - t_{ON} : 120 ns
- Low Charge Injection - Q : - 1 pC
- TTL/CMOS-Compatible Logic
- Single Supply Capability
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Less Signal Errors and Distortion
- Reduced Power Supply Requirements
- Faster Throughput
- Reduced Pedestal Errors
- Simple Interfacing

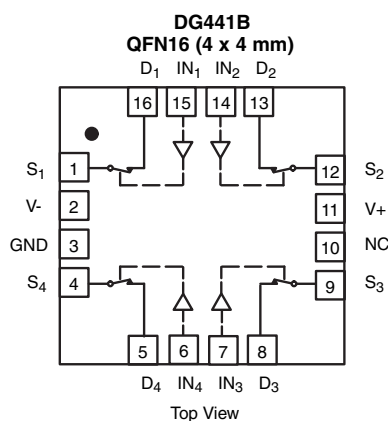
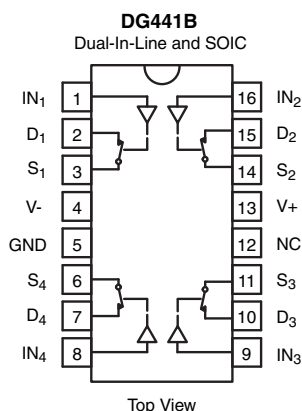
APPLICATIONS

- Audio Switching
- Data Acquisition
- Sample-and-Hold Circuits
- Communication Systems
- Automatic Test Equipment
- Medical Instruments



RoHS
COMPLIANT
HALOGEN
FREE

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE

Logic	DG441B	DG442B
0	ON	OFF
1	OFF	ON

Logic "0" $\leq 0.8\text{ V}$

Logic "1" $\geq 2.4\text{ V}$

ORDERING INFORMATION

Temp Range	Package	Part Number
- 40 °C to 85 °C	16-pin Plastic DIP	DG441BDJ
		DG441BDJ-E3
		DG442BDJ
		DG442BDJ-E3
	16-pin Narrow SOIC	DG441BDY-E3
		DG441BDY-T1-E3
		DG442BDY-E3
		DG442BDY-T1-E3
	16 pin QFN 4 x 4 mm (Variation 1)	DG441BDN-T1-E4
		DG442BDN-T1-E4

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ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
V+ to V-		44	V
GND to V-		25	
Digital Inputs ^a , V_S , V_D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first	
Continuous Current (Any Terminal)		30	mA
Current, S or D (Pulsed at 1 ms, 10 % duty cycle)		100	
Storage Temperature		- 65 to 125	$^{\circ}\text{C}$
Power Dissipation (Package) ^b	16-pin Plastic DIP ^c	470	mW
	16-pin Narrow Body SOIC ^d	900	
	QFN-16 ^d	850	

Notes:

a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC Board.

c. Derate 6 mW/ $^{\circ}\text{C}$ above 75 $^{\circ}\text{C}$.

d. Derate 12 mW/ $^{\circ}\text{C}$ above 75 $^{\circ}\text{C}$.



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SPECIFICATIONS ^a (for dual supplies)							
Parameter	Symbol	Test Conditions Unless Otherwise Specified V ₊ = 15 V, V ₋ = - 15 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^e	Temp. ^b	Limits - 40 °C to 85 °C			Unit
				Min. ^d	Typ. ^c	Max. ^d	
Analog Switch							
Analog Signal Range ^e	V _{ANALOG}		Full	- 15		15	V
Drain-Source On-Resistance	R _{DS(on)}	I _S = 1 mA, V _D = ± 10 V	Room Full		45	80 95	Ω
On-Resistance Match Between Channels ^e	ΔR _{DS(on)}	I _S = 1 mA, V _D = ± 10 V	Room Full		2	4 5	
Switch Off Leakage Current	I _{S(off)}	V _D = ± 14 V, V _S = ± 14 V	Room Full	- 0.5 - 5	± 0.01	0.5 5	nA
	I _{D(off)}		Room Full	- 0.5 - 5	± 0.01	0.5 5	
Channel On Leakage Current	I _{D(on)}	V _S = V _D = ± 14 V	Room Full	- 0.5 - 10	± 0.02	0.5 10	
Digital Control							
Input Voltage Low	V _{INL}		Full			0.8	V
Input Voltage High	V _{INH}		Full	2.4			
Input Current V _{IN} Low	I _{INL}	V _{IN} under test = 0.8 V All Other = 2.4 V	Full	- 1	- 0.01	1	μA
Input Current V _{IN} High	I _{INH}	V _{IN} under test = 2.4 V All Other = 0.8 V	Full	- 1	0.01	1	
Dynamic Characteristics							
Turn-On Time	t _{ON}	R _L = 1 kΩ, C _L = 35 pF V _S = 10 V, See Figure 2	Room		120	220	ns
Turn-Off Time	t _{OFF}		Room		65	120	
Charge Injection ^e	Q	C _L = 1 nF, V _S = 0 V V _{gen} = 0 V, R _{gen} = 0 Ω	Room		- 1		pC
Off Isolation ^e	OIRR	R _L = 50 Ω , C _L = 15 pF V _S = 1 V _{RMS} , f = 100 kHz	Room		- 90		dB
Crosstalk (Channel-to-Channel)	X _{TALK}		Room		- 95		
SourceOff Capacitance ^e	C _{S(off)}	f = 1 MHz	Room		4		pF
Drain Off Capacitance ^e	C _{D(off)}		Room		4		
Channel On Capacitance ^e	C _{D(on)}	V _S = V _D = 0 V, f = 1 MHz	Room		16		
Power Supplies							
Positive Supply Current	I ₊	V ₊ = 16.5 V, V ₋ = - 16.5 V V _{IN} = 0 or 5 V	Room Full			1 5	μA
Negative Supply Current	I ₋		Room Full	- 1 - 5			

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SPECIFICATIONS (for single supply)							
Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 12 V, V- = 0 V VIN = 2.4 V, 0.8 V ^e	Temp. ^b	Limits - 40 °C to 85 °C			Unit
				Min. ^d	Typ. ^c	Max. ^d	
Analog Switch							
Analog Signal Range ^e	V _{ANALOG}		Full	0		12	V
Drain-Source On-Resistance	R _{DS(on)}	I _S = 1 mA, V _D = 3 V, 8 V	Room Full		90	160 200	Ω
Dynamic Characteristics							
Turn-On Time	t _{ON}	R _L = 1 kΩ, C _L = 35 pF, V _S = 8 V See Figure 2	Room		120	300	ns
Turn-Off Time	t _{OFF}		Room		60	200	
Charge Injection	Q	C _L = 1 nF, V _{gen} = 6 V, R _{gen} = 0 Ω	Room		4		pC
Power Supplies							
Positive Supply Current	I+	VIN = 0 V or 5 V	Room Full			1 5	μA
Negative Supply Current	I-		Room Full	- 1 - 5			

Notes:

a. Refer to PROCESS OPTION FLOWCHART.

b. Room = 25 °C, Full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

e. Guaranteed by design, not subject to production test.

f. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SCHEMATIC DIAGRAM (typical channel)

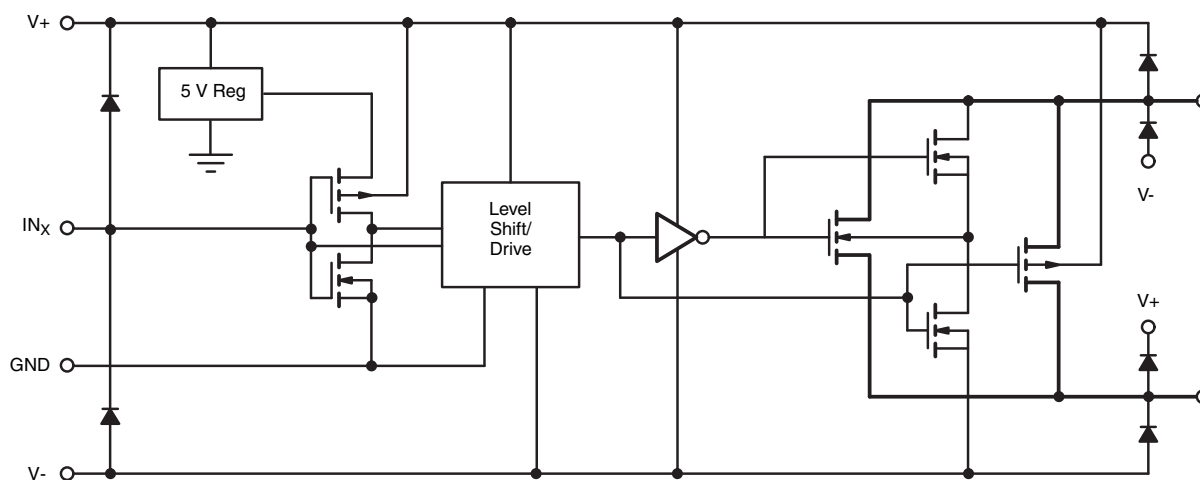


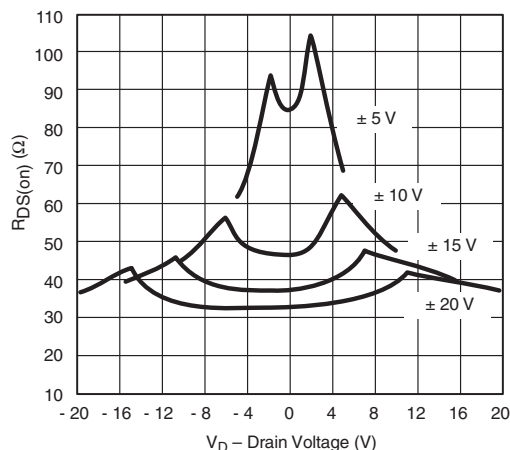
Figure 1.



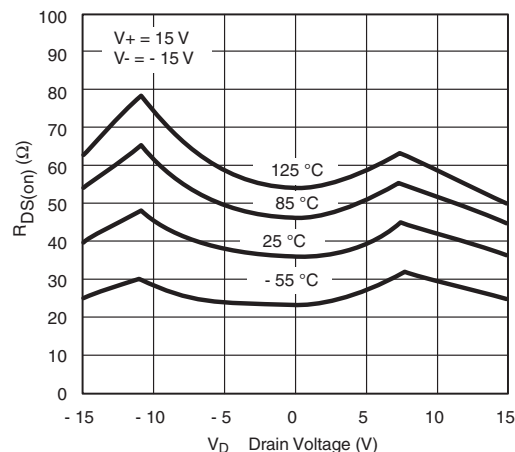
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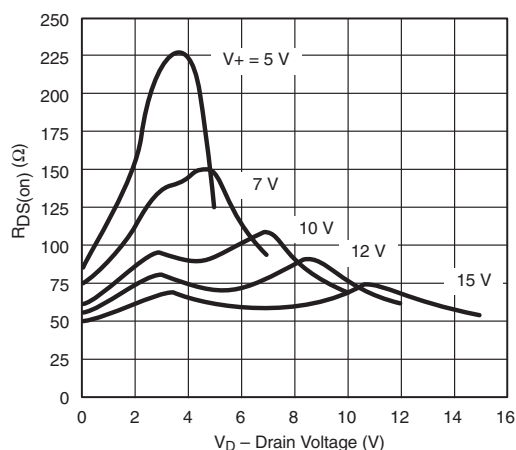
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



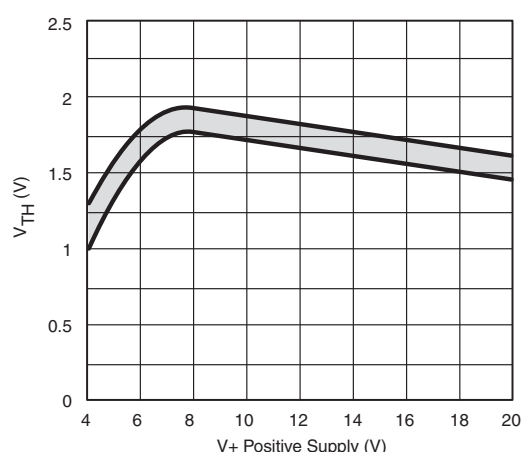
$R_{DS(on)}$ vs. V_D and Power Supply Voltages



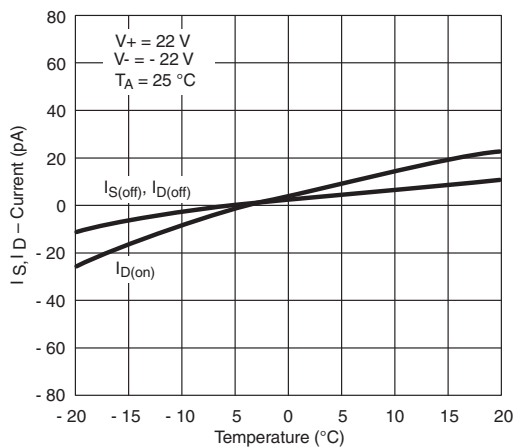
$R_{DS(on)}$ vs. V_D and Temperature



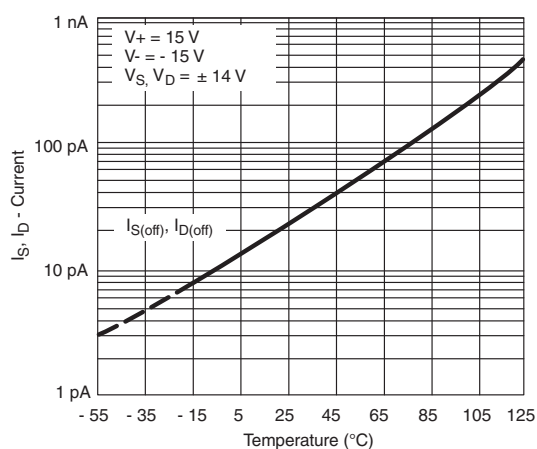
$R_{DS(on)}$ vs. V_D and Single Power Supply Voltages



Input Switching Threshold vs. Supply Voltage



Leakage Currents vs. Analog Voltage



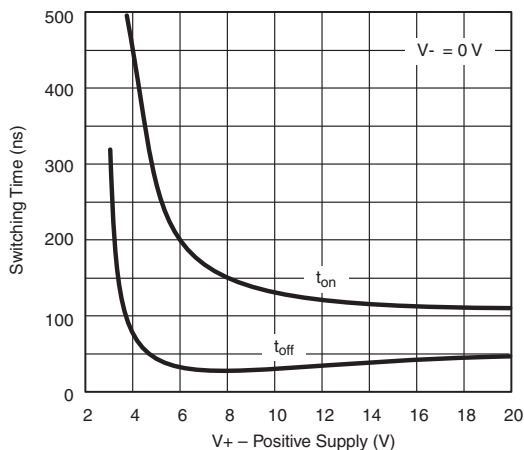
Leakage Currents vs. Temperature

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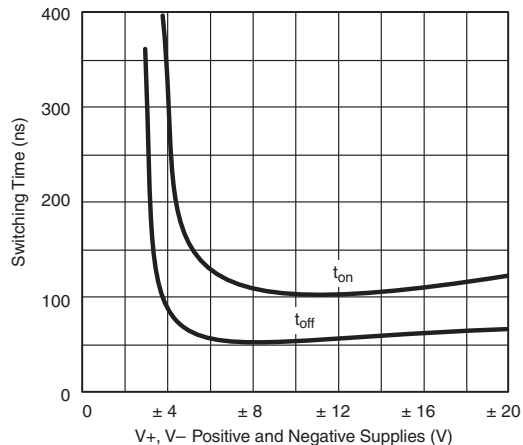
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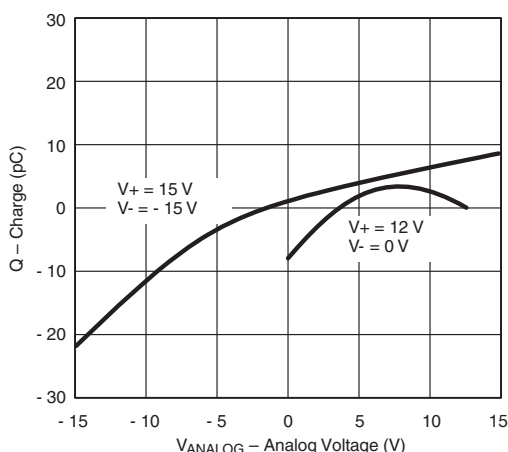
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



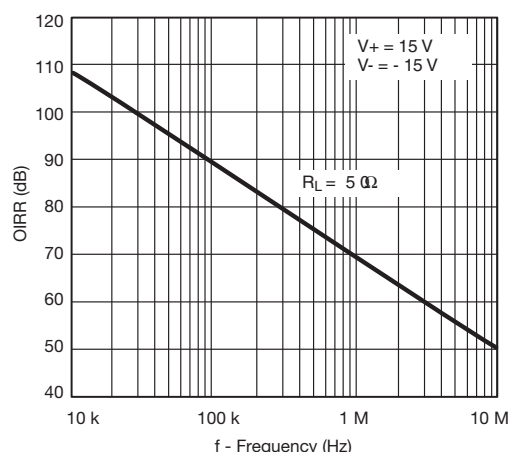
Switching Time vs. Single Supply Voltage



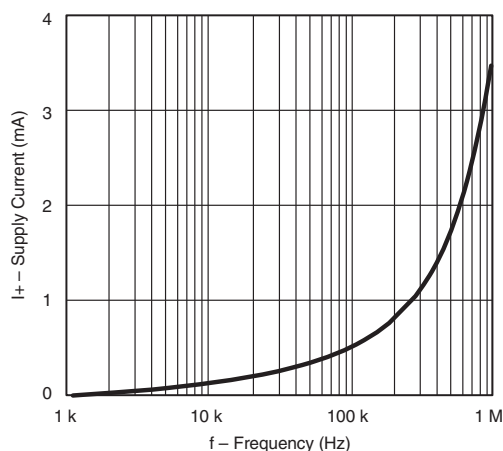
Switching Times vs. Power Supply Voltage



Q_S , Q_D - Charge Injection vs. Analog Voltage



Off Isolation vs. Frequency



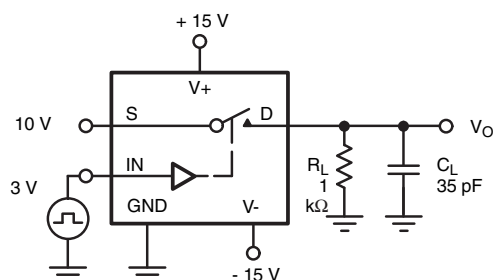
Supply Current vs. Switching Frequency



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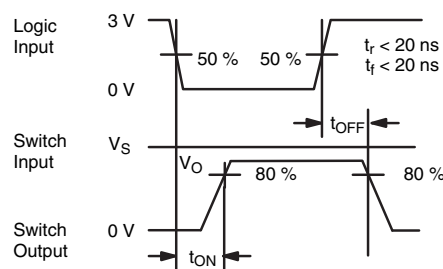
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TEST CIRCUITS



C_L (includes fixture and stray capacitance)

Figure 2. Switching Time



Note: Logic input waveform is inverted for DG442.

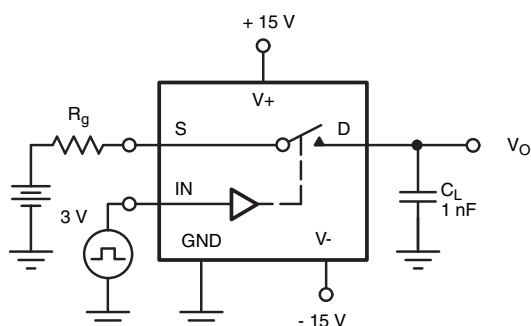
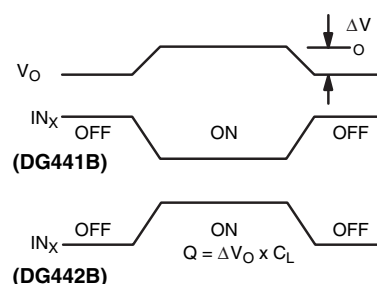
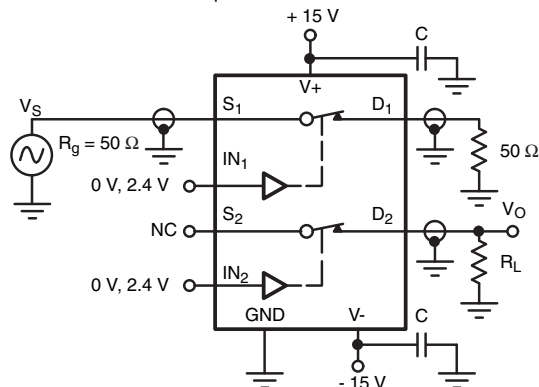


Figure 3. Charge Injection

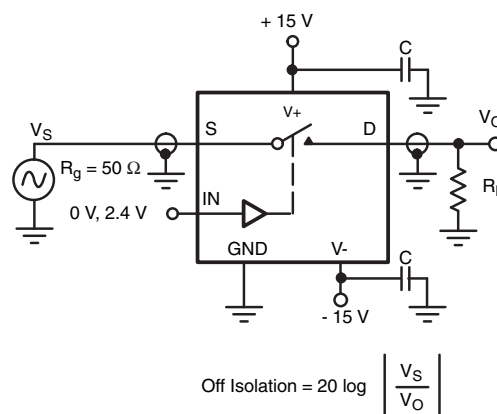


$C = 1$ mF tantalum in parallel with 0.01 mF ceramic



$X_{TALK} \text{ Isolation} = 20 \log \left| \frac{V_S}{V_O} \right|$
C = RF bypass

Figure 4. Crosstalk



Off Isolation = $20 \log \left| \frac{V_S}{V_O} \right|$

Figure 5. Off Isolation

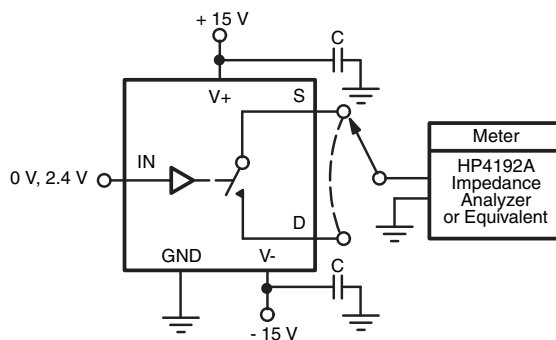


Figure 6. Source/Drain Capacitances

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APPLICATIONS

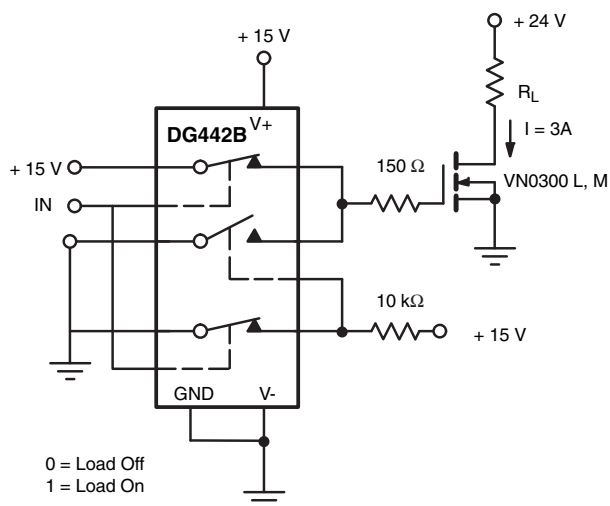


Figure 7. Power MOSFET Driver

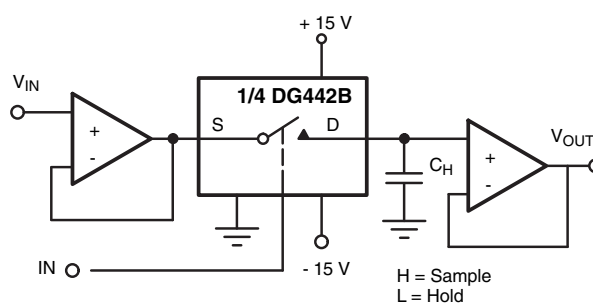


Figure 8. Open Loop Sample-and-Hold

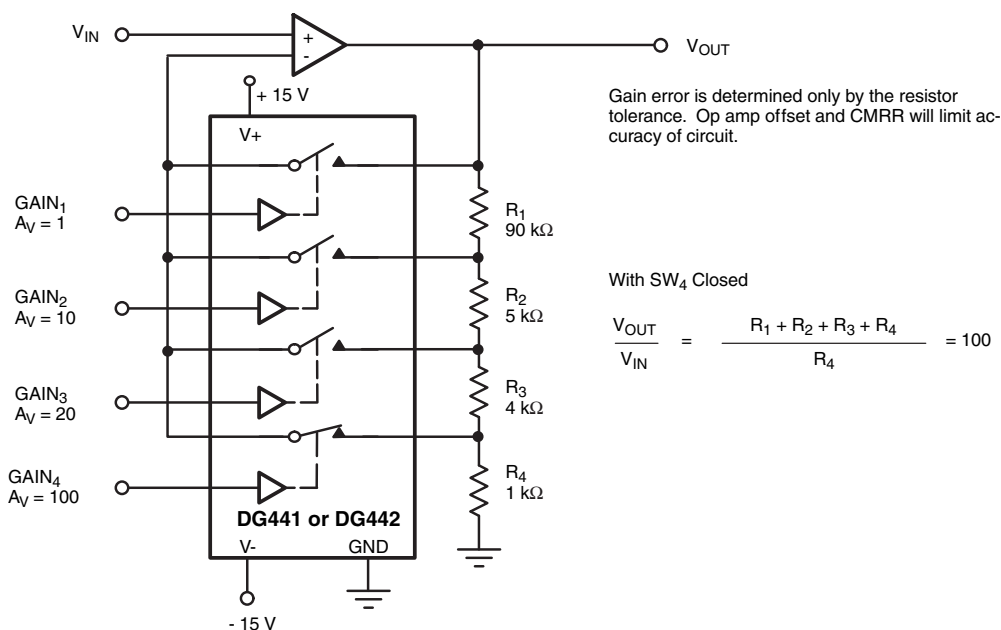


Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72625.

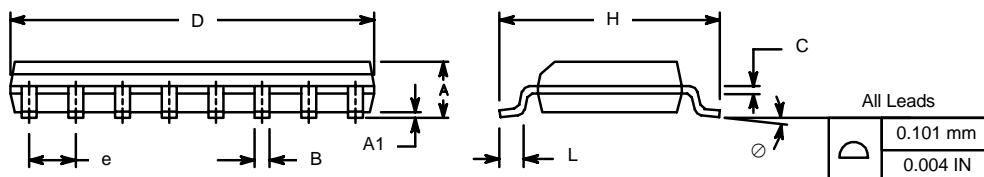
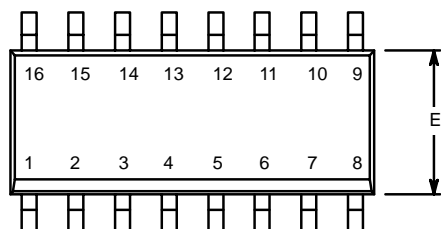


Package Information

Vishay Siliconix

SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.38	0.51	0.015	0.020
C	0.18	0.23	0.007	0.009
D	9.80	10.00	0.385	0.393
E	3.80	4.00	0.149	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.50	0.93	0.020	0.037
Ø	0°	8°	0°	8°

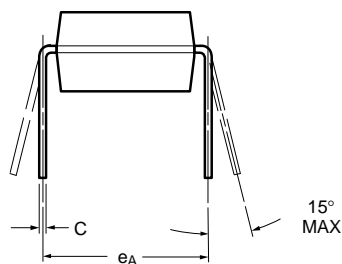
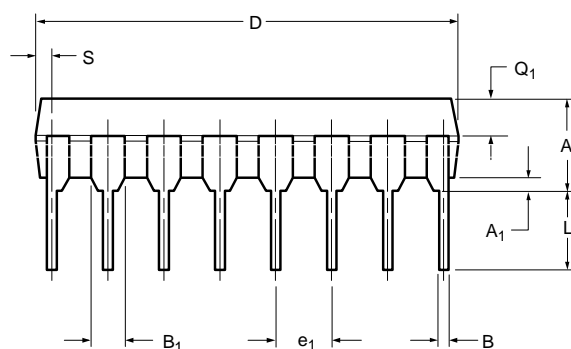
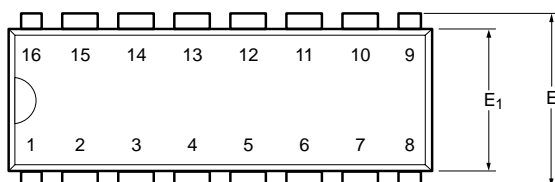
ECN: S-03946—Rev. F, 09-Jul-01
DWG: 5300



Package Information

Vishay Siliconix

PDIP: 16-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	3.81	5.08	0.150	0.200
A₁	0.38	1.27	0.015	0.050
B	0.38	0.51	0.015	0.020
B₁	0.89	1.65	0.035	0.065
C	0.20	0.30	0.008	0.012
D	18.93	21.33	0.745	0.840
E	7.62	8.26	0.300	0.325
E₁	5.59	7.11	0.220	0.280
e₁	2.29	2.79	0.090	0.110
e_A	7.37	7.87	0.290	0.310
L	2.79	3.81	0.110	0.150
Q₁	1.27	2.03	0.050	0.080
S	0.38	1.52	.015	0.060
ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482				

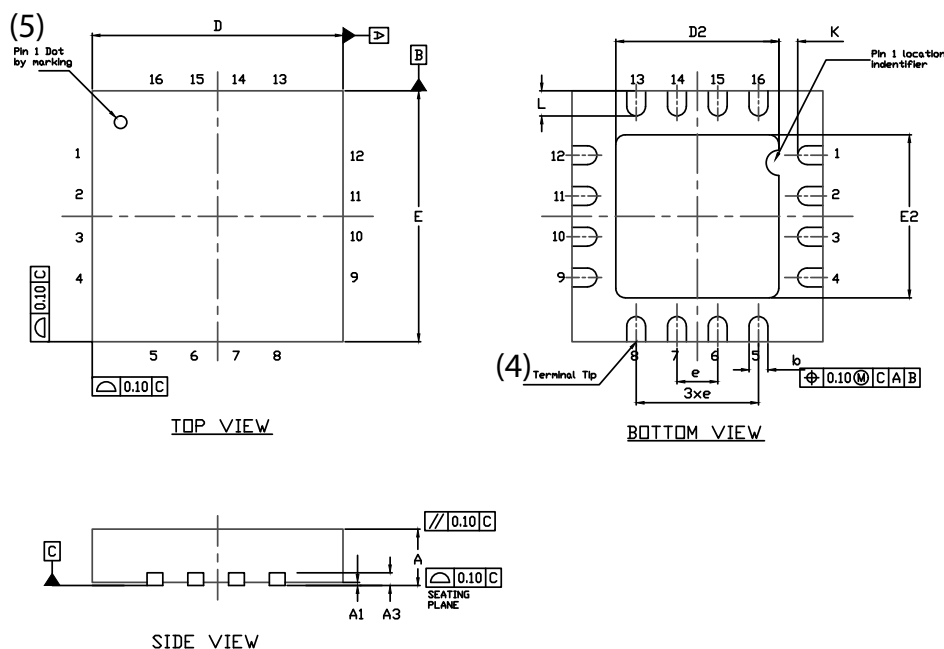


www.vishay.com

Package Information

Vishay Siliconix

QFN 4x4-16L Case Outline



DIM	VARIATION 1						VARIATION 2					
	MILLIMETERS ⁽¹⁾			INCHES			MILLIMETERS ⁽¹⁾			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
A3	0.20 ref.			0.008 ref.			0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014
D	4.00 BSC			0.157 BSC			4.00 BSC			0.157 BSC		
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
E	4.00 BSC			0.157 BSC			4.00 BSC			0.157 BSC		
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
K	0.20 min.			0.008 min.			0.20 min.			0.008 min.		
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020
N ⁽³⁾	16			16			16			16		
Nd ⁽³⁾	4			4			4			4		
Ne ⁽³⁾	4			4			4			4		

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. - 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

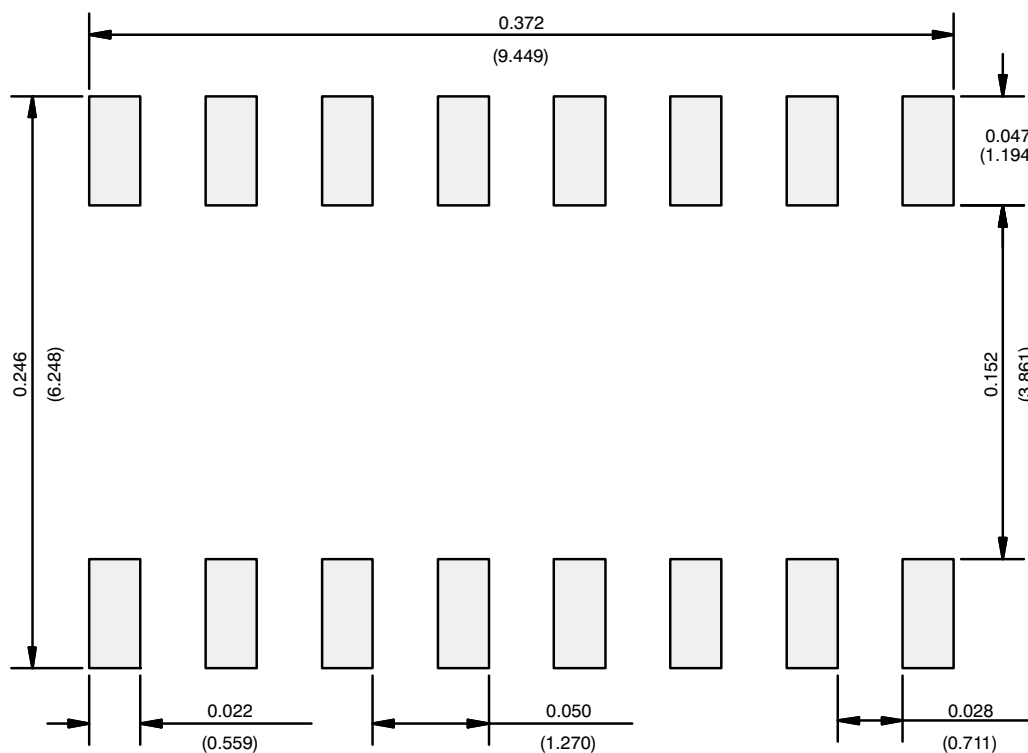
ECN: S13-0893-Rev. B, 22-Apr-13
DWG: 5890

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads
Dimensions in Inches/(mm)

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